G2N5401 PNP EPITAXIAL PLANAR TANSISTOR

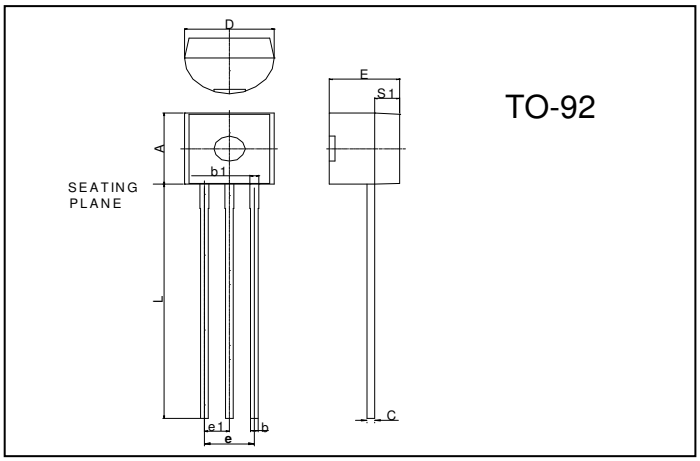
Description

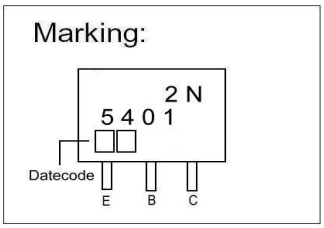
The G2N5401 is designed for general purpose applications requiring high breakdown voltages.

Features

*Complementary to NPN Type G2N5551
*High Collector-Emitter Breakdown Voltage (V_{CEO}=150V@I_C=1mA))

Package Dimensions





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.45	4.7	D	4.44	4.7
S_1	1.02	-	E	3.30	3.81
b	0.36	0.51	L	12.70	-
b_1	0.36	0.76	e1	1.150	1.390
C	0.36	0.51	e	2.42	2.66

Absolute Maximum Ratings at Ta = 25℃

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	℃
Storage Temperature	Tstg	-55 ~ +150	℃
Collector to Base Voltage	V_{CBO}	-160	V
Collector to Emitter Voltage	V_{CEO}	-150	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-600	mA
Total Power Dissipation	P_D	625	mW

Characteristics at Ta = 25℃

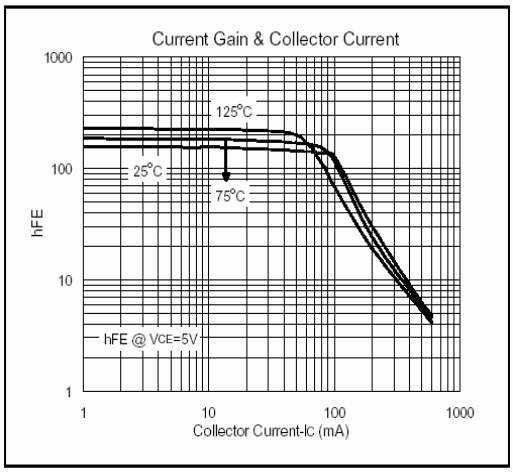
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	-160	-	-	V	I_C=-100uA,I_E=0
BV_{CEO}	-150	-	-	V	I_C=-1mA,I_B=0
BV_{EBO}	-5	-	-	V	I_E=-10uA,I_C=0
I_{CBO}	-	-	-50	nA	V_{CB}=-120V, I_E=0
I_{EBO}	-	-	-50	nA	V_{EB}=-3V, I_C=0
*V_{CE}(sat)1	-	-	-0.2	V	I_C=-10mA, I_B=-1mA
*V_{CE}(sat)2	-	-	-0.5	mV	I_C=-50mA, I_B=-5mA
*V_{BE}(sat)1	-	-	-1	V	I_C=-10mA, I_B=-1mA
*V_{BE}(sat)2	-	-	-1	V	I_C=-50mA, I_B=-5mA
*hFE1	50	-	-		V_{CE}=-5V, I_B=-1mA
*hFE2	80	160	400		V_{CE}=-5V, I_C=-10mA
*hFE3	50	-	-		V_{CE}=-5V, I_C=-50mA
fT	100	-	300	MHz	V_{CE}=-10V, I_C=-10mA, f=100MHz
Cob	-	-	6	pF	V_{CB}=-10V, f=1MHz, IE=0

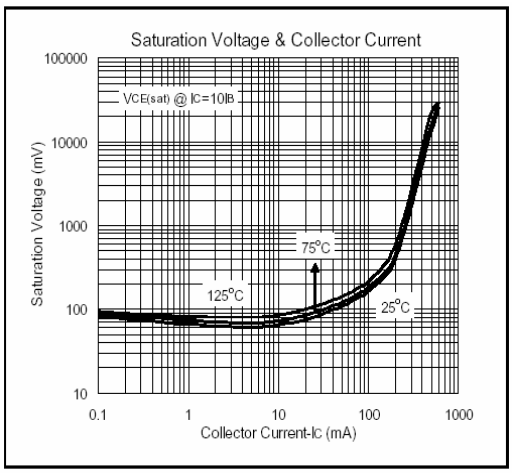
* Pulse Test: Pulse Width≦380us, Duty Cycle≦2%

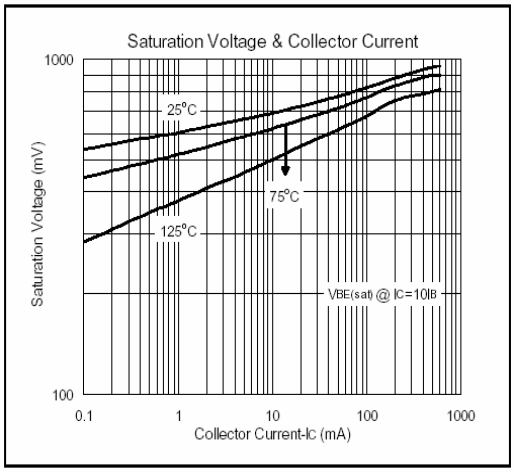
Classification Of h_{FE2}

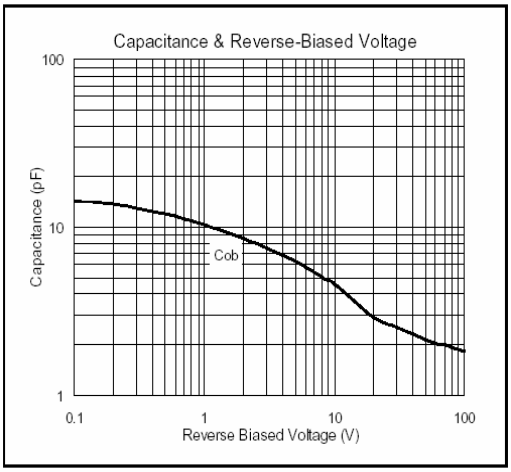
Rank	A	N	C
Range	80-200	100-240	160-400

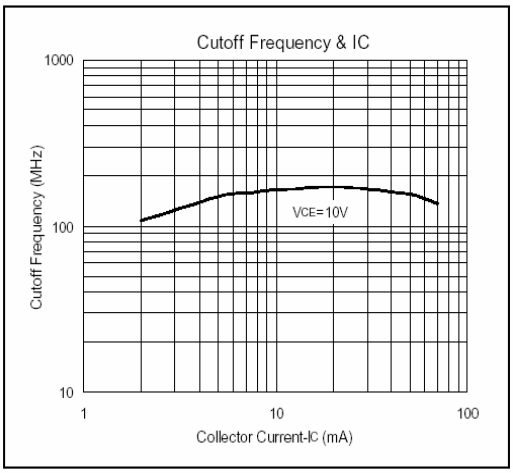
Characteristics Curve

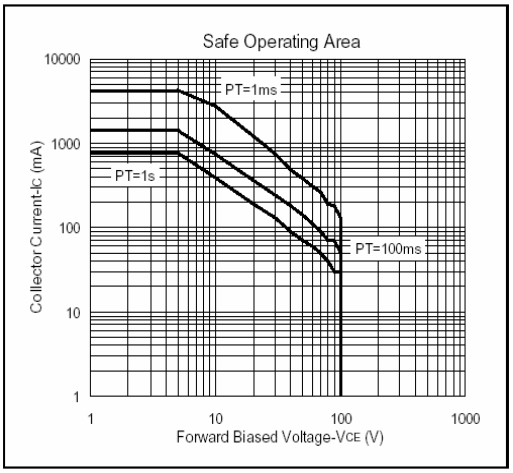


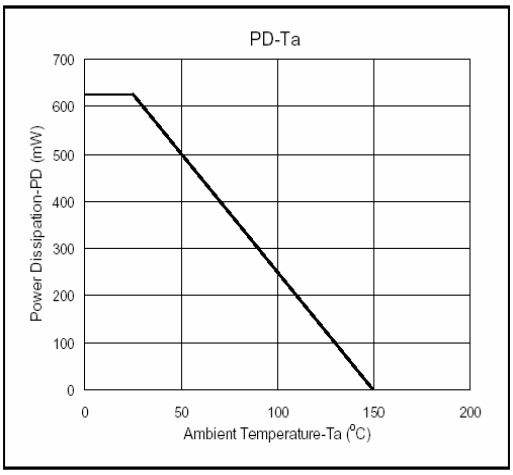












Head Office And Factory:
- **Taiwan**: No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
  TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- **China**: (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China
  TEL : 86-21-5895-7671 ~ 4 FAX : 86-21-38950165